



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

30A02CH — PNP Epitaxial Planar Silicon Transistor Low-Frequency General-Purpose Amplifier Applications

Applications

- Low-frequency Amplifier, high-speed switching, small motor drive

Features

- Large current capacitance
- Low collector-to-emitter saturation voltage (resistance) $R_{CE(sat)}$ typ.=580m Ω [$I_C=0.7A$, $I_B=35mA$]
- Small ON-resistance (R_{on})

Specifications

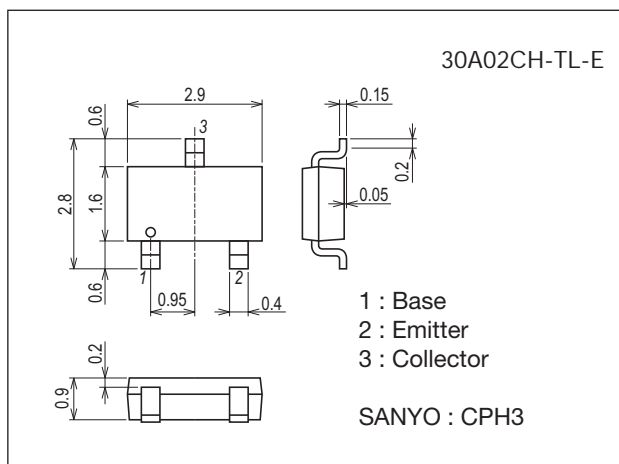
Absolute Maximum Ratings at $T_a=25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		-30	V
Collector-to-Emitter Voltage	V_{CEO}		-30	V
Emitter-to-Base Voltage	V_{EBO}		-5	V
Collector Current	I_C		-700	mA
Collector Current (Pulse)	I_{CP}		-1.4	A
Collector Dissipation	P_C	Mounted on a ceramic board (600mm ² ×0.8mm)	700	mW
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Package Dimensions

unit : mm (typ)

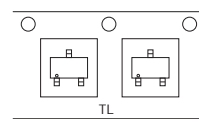
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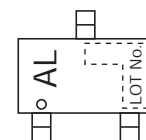
Product & Package Information

- Package : CPH3
- JEITA, JEDEC : SC-59, TO-236, SOT-23
- Minimum Packing Quantity : 3,000 pcs./reel

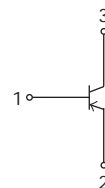
Packing Type: TL



Marking



Electrical Connection

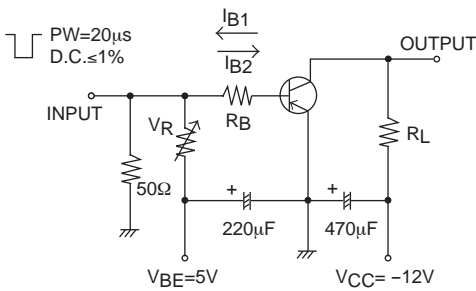


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Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = -30\text{V}, I_E = 0\text{A}$			-100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0\text{A}$			-100	nA
DC Current Gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -10\text{mA}$	200		500	
Gain-Bandwidth Product	f_T	$V_{CE} = -10\text{V}, I_C = -50\text{mA}$		520		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}, f = 1\text{MHz}$		4.7		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -200\text{mA}, I_B = -10\text{mA}$		-110	-220	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -200\text{mA}, I_B = -10\text{mA}$		-0.9	-1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0\text{A}$	-30			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, R_{BE} = \infty$	-30			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0\text{A}$	-5			V
Turn-On Time	t_{on}	See specified Test Circuit.		35		ns
Storage Time	t_{stg}			125		ns
Fall Time	t_f			25		ns

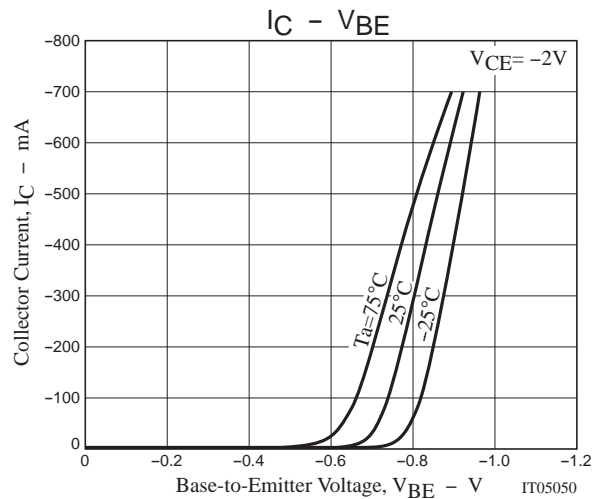
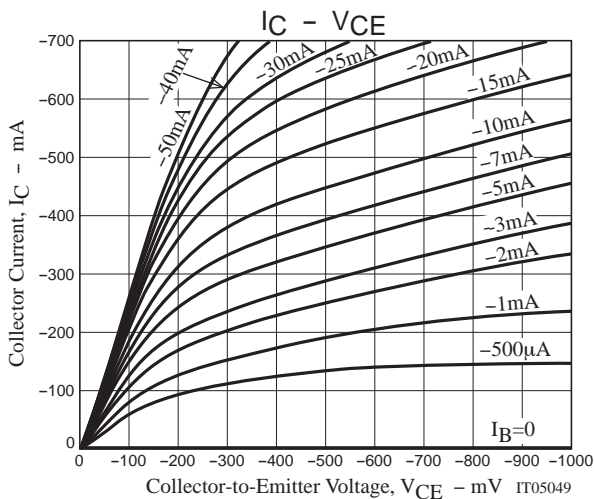
Switching Time Test Circuit



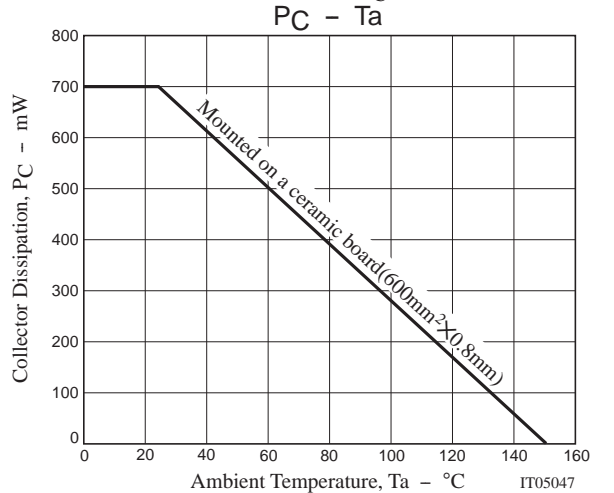
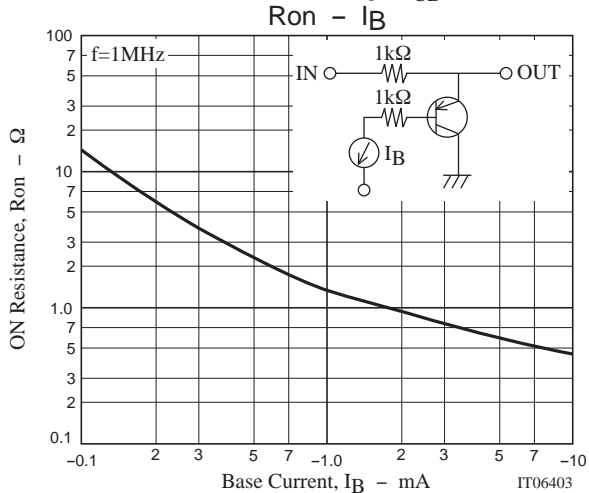
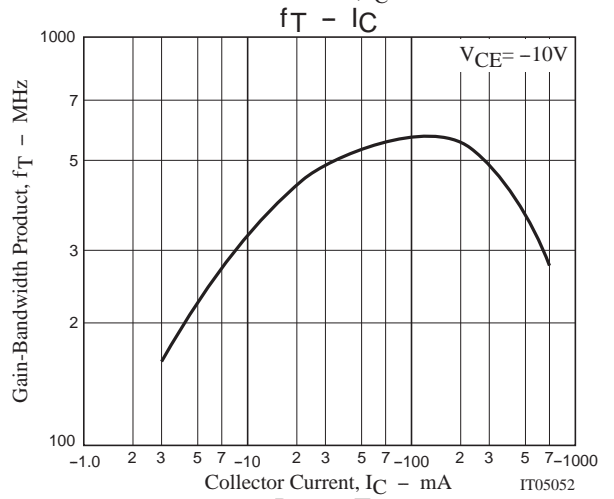
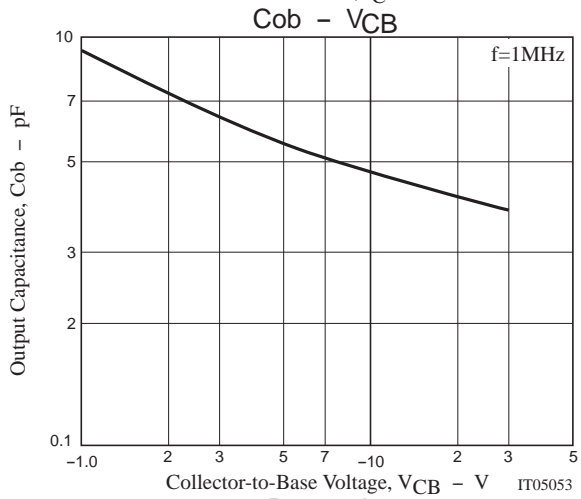
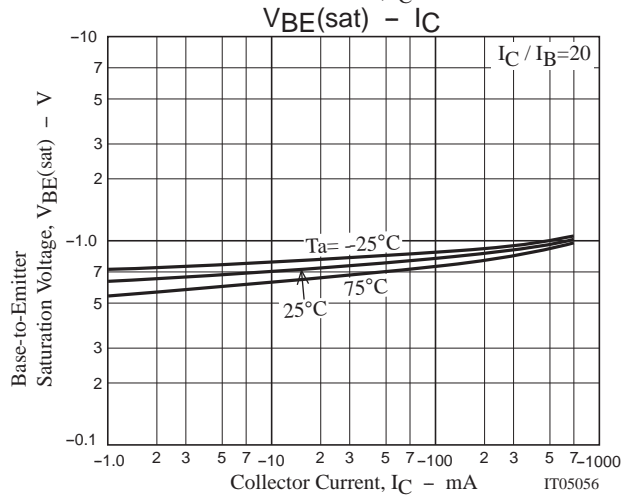
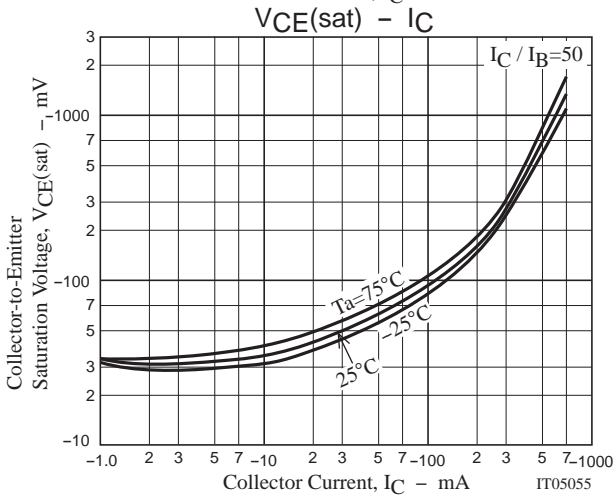
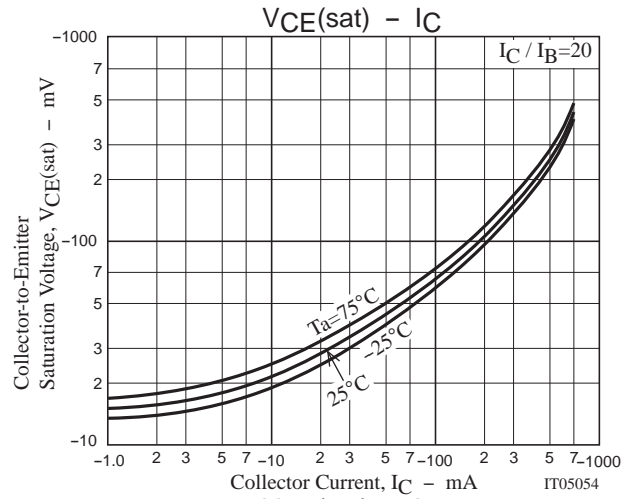
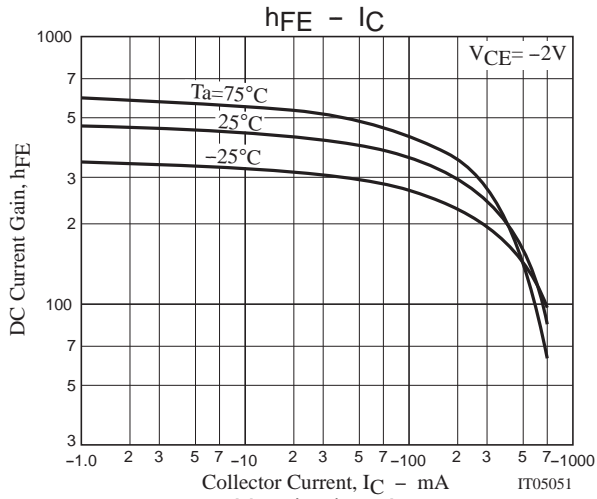
$$I_C = 20I_{B1} = -20I_{B2} = -300\text{mA}$$

Ordering Information

Device	Package	Shipping	memo
30A02CH-TL-E	CPH3	3,000pcs./reel	Pb Free



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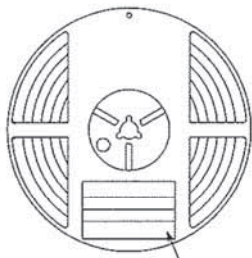
Embossed Taping Specification

30A02CH-TL-E

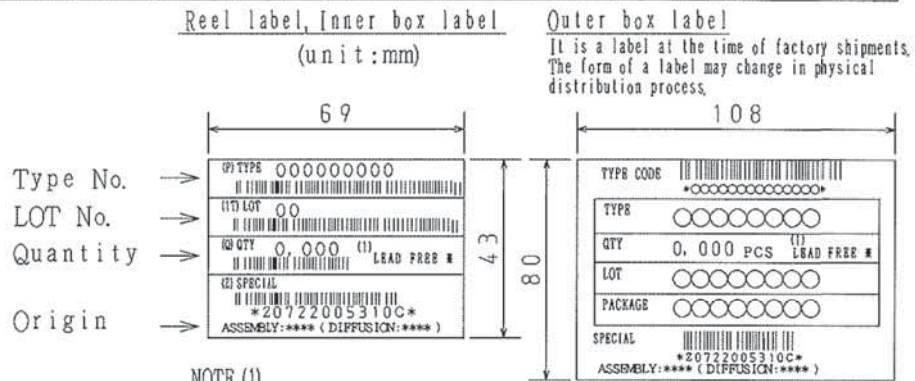
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
CPH3	CPH3	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



Reel label



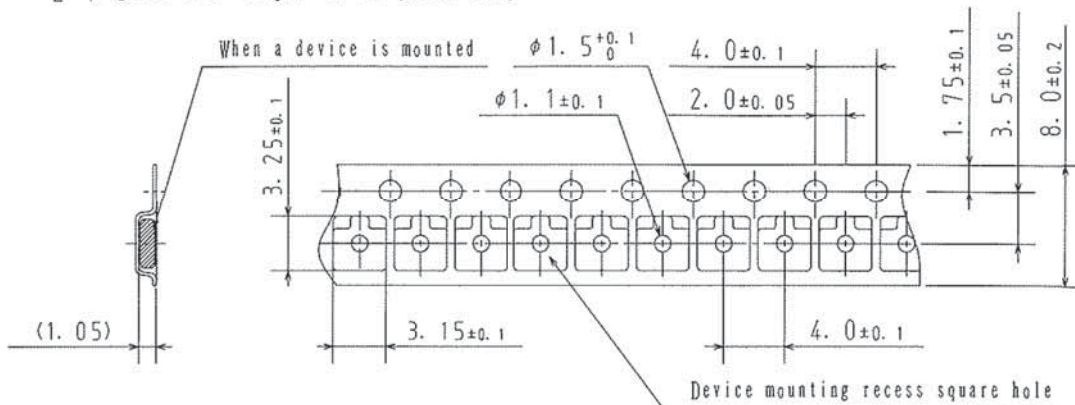
NOTE (1)

The LEAD FREE # description shows that the surface treatment of the terminal is lead free.

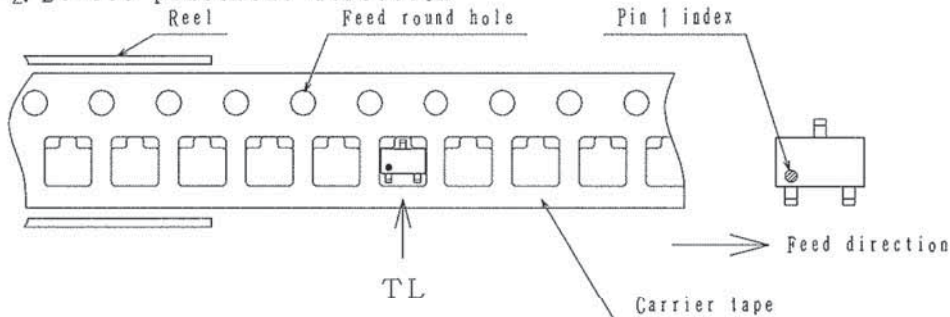
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

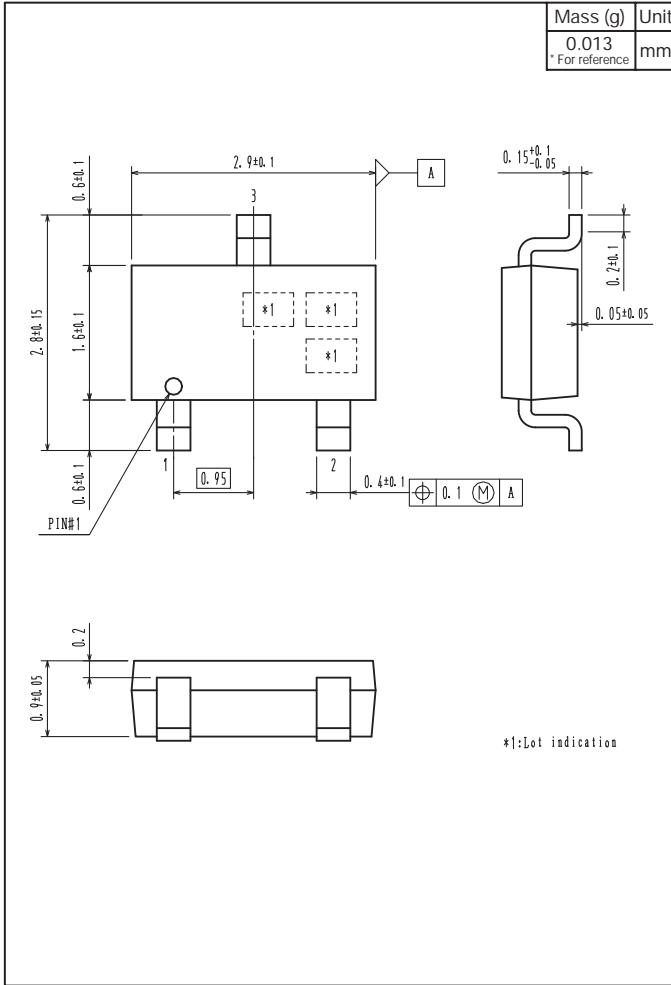


Those with one electrode terminal on the feed hole side.....TL

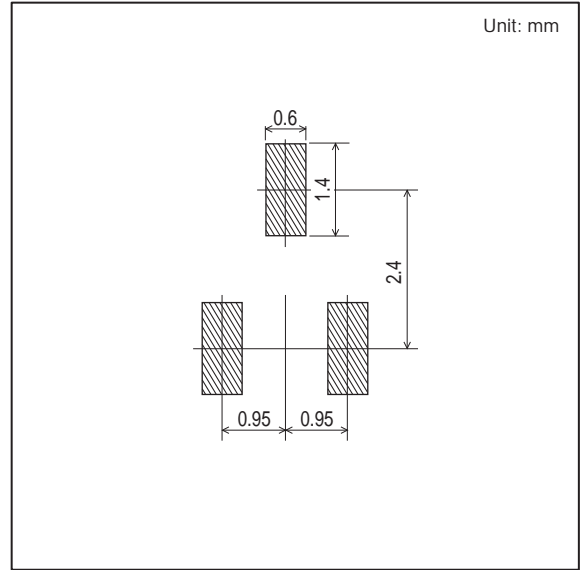
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Outline Drawing

30A02CH-TL-E



Land Pattern Example



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